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Complete if Known

Application Number	09/932.239
Filing Date	17 August 2001
First Named Inventor	Christophe Pierrat et al.
Group Art Unit	1756
Examiner Name	Unassigned
Attorney Docket Number	NMTI 1002-3

(use as many sheets as necessary)

Sheet	1	of	1
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INFORMATION DISCLOSURE
CITATION

PTO-1449

Atty. Docket No.

NMTI 1002-3

Serial No.

09/932,239

Applicant

PIERRAT, Christophe

Filing Date

8/17/2001

Group

1756

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SRM	6,420,074 B2	7/16/2002	Wang et al.	430	5	12/7/2000
SRM	6,436,590 B2	8/20/2002	Wang, et al.	430	5	4/20/2001
SRM	2002/0083410 A1	6/27/2002	Wu, et al.	716	19	12/5/2001
SRM	2002/0122994 A1	9/5/2002	Cote, et al.	430	5	2/28/2002
SRM	2002/0127479 A1	9/12/2002	Pierrat	430	5	2/6/2002
SRM	2002/0129327 A1	9/12/2002	Pierrat, et al.	716	19	11/15/2001
SRM	2002/0136964 A1	9/26/2002	Pierrat	430	5	3/23/2001
SRM	2002/0142231 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
SRM	2002/0142232 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
SRM	2002/0144232 A1	10/3/2002	Ma, et al.	716	21	5/31/2001
SRM	2002/0152454 A1	10/17/2002	Cote, et al.	716	21	6/7/2002
SRM	2002/0155363 A1	10/24/2002	Cote, et al.	430	5	6/7/2002

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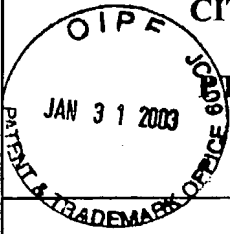
1756

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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SRM	WO 02/073312 A1	9/19/2002	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>

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INFORMATION DISCLOSURE CITATION  TO-1449		Atty. Docket No. NMTI 1002-3 Applicant PIERRAT, Christophe Filing Date 8/17/2001	Serial No. 09/932,239 Group 1756
RECEIVED FEB 04 2003 TC 1700			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
<i>SKM</i>	Cooke, M., "OPC/PSM Designs For Poly Gate Layers", European Semiconductor, Vol. 22, No. 7, pp. 57-59, July 2000.		
<i>SKM</i>	Granik, Y., et al., "Sub-Resolution Process Windows And Yield Estimation Technique Based On Detailed Full-Chip CD Simulation", SPIE, Vol. 4182, pp. 335-341 (2000).		
<i>SKM</i>	Plat, M., et al., "The Impact of Optical Enhancement Techniques on the Mask Error Enhancement Function (MEEF)", SPIE, Vol. 4000, pp. 206-214, March 1-3, 2000.		
<i>SKM</i>	Mansuripur, M., et al., "Projection Photolithography", Optics & Photonics News 11, 17 pages, February 2000.		

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INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NMTI 1002-3		Serial No. 09/932.239		
		Applicant PIERRAT, Christophe		Group 1754		
		Filing Date 8/17/2001		Not Yet Assigned		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SRM	5,472,814	12/5/1995	Lin	430	5	11/17/1994
SRM	5,923,562	7/13/1999	Liebmann, et al.	364	488	10/18/1996
SRM	6,130,012	10/10/2000	May, et al.	430	5	1/13/1999
SRM	6,139,994	10/31/2000	Broeke, et al.	430	5	6/25/1999
SRM	6,185,727 B1	2/6/2001	Liebmann	716	19	12/12/1995
SRM	6,335,128 B1	1/1/2002	Cobb, et al.	430	5	9/28/1999
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SRM	2001/0000240 A1	4/12/2001	Wang, et al.	430	5	12/7/2000
SRM	2001/0028985 A1	10/11/2001	Wang, et al.	430	5	4/20/2001

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		Applicant PIERRAT, Christophe		Group 1754 Not Yet Assigned			
		Filing Date 8/17/2001					
FOREIGN PATENT DOCUMENTS							
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SRM	WO 01/23961 A1	4/5/2001	WO	1	—	<input type="checkbox"/>	<input type="checkbox"/>
SRM	WO 02/03140 A1	1/10/2002	WO	1	—	<input type="checkbox"/>	<input type="checkbox"/>
SRM	JP 2-140743	5/30/1990	JP	1	—	<input checked="" type="checkbox"/>	<input type="checkbox"/>
SKL	GB 2,333,613 A	7/28/1999	GB	1	—	<input type="checkbox"/>	<input type="checkbox"/>
SRM	WO 98/12605 A1	3/26/1998	WO	1	—	<input type="checkbox"/>	<input type="checkbox"/>

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		NMTI 1002-3	09/932,239
		Applicant	
		PIERRAT, Christophe	
		Filing Date	Group
		8/17/2001	1756 Not Yet Assigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
SPM	Polarized Wang, R., et al., "Polarized Phase Shift Mask: Concept, Design, and Potential Advantages to Photolithography Process and Physical Design", Motorola Semiconductor Product Sector (12 pages).		
	Ogawa, K., et al., "Phase Defect Inspection by Differential Interference", Lasertec Corporation (12 pages).		
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	Wong, A., et al., "Polarization Effects in Mask Transmission", University of California Berkeley (8 pages).		
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SPM	Terasawa, T., et al., "Imaging Characteristics of Multi-Phase-Shifting and Halftone Phase-Shifting Masks", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 2991-2997, November 1991.		
SPM	Inoue, S., et al., "Simulation Study on Phase-Shifting Masks for Isolated Patterns", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3010-3015, November 1991.		
SPM	Watanabe, H., et al., "Detection and Printability of Shifter Defects in Phase-Shifting Masks", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3016-3020, November 1991.		
SPM	Watanabe, H., et al., "Pattern Transfer Characteristics of Transparent Phase Shifting Mask", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3004-3009, November 1991.		
SPM	Moriwa, A., et al., "Algorithm for Phase-Shift Mask Design with Priority on Shifter Placement", Jpn. J. Appl. Phys., Vol. 32, Pt. 1, No. 12B, pp. 5874-5879, December 1993.		
SPM	Ooi, K., et al., "Computer Aided Design Software for Designing Phase-Shifting Masks", Jpn. J. Appl. Phys., Vol. 32, Pt. 1, No. 12B, pp. 5887-5891, December 1993.		
SPM	Ohtsuka, H., et al., "Evaluation of Repair Phase and Size Tolerance for a Phase-Shift Mask", J. Vac. Sci. Technol., Vol. 11, No. 6, pp. 2665-2668, November/December 1993.		

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NMTI 1002-3	Serial No. 09/932,239
	Applicant PIERRAT, Christophe	Group 1756
	Filing Date 8/17/2001	Not Yet Assigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
EXAMINER'S INITIALS	CITATION	
<i>SPM</i>	Moniwa, A., et al., "Heuristic Method for Phase-Conflict Minimization in Automatic Phase-Shift Mask Design", Jpn. J. Appl. Phys., Vol. 34, Pt. 1, No. 12B, pp. 6584-6589, December 1995.	
<i>SPM</i>	Ohnuma, H., et al., "Lithography Computer Aided Design Technology for Embedded Memory in Logic", Jpn. J. Appl. Phys., Vol. 37, Part I, No. 12B, pp. 6686-6688, December 1998.	
<i>SPM</i>	Kikuchi, K., et al., "Method of Expanding Process Window for the Double Exposure Technique with alt-PSMs", Optical Microlithography XIII, Proceeding of SPIE, Vol. 4000, pp. 121-131 (2000).	

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			Applicant PIERRAT, Christophe		Group 1756 Not Yet Assigned	
			Filing Date 8/17/2001			
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SRM	4,037,918	7/26/1977	Kato	350	3.5	7/31/1975
SRM	4,456,371	6/26/1984	Lin	355	71	6/30/1982
SRM	5,302,477	4/12/1994	Dao, et al.	430	5	8/21/1992
SRM	5,308,741	5/3/1994	Kemp	430	312	7/31/1992
SRM	5,316,878	5/31/1994	Saito, et al.	430	5	6/4/1992
SRM	5,324,600	6/28/1994	Jinbo, et al.	430	5	7/7/1992
SRM	5,328,807	7/12/1994	Tanaka, et al.	430	311	6/7/1991
SRM	5,334,542	8/2/1994	Saito, et al.	437	40	11/18/1992
SRM	5,352,550	10/4/1994	Okamoto	430	5	4/23/1993
SRM	5,364,716	11/15/1994	Nakagawa, et al.	430	5	9/3/1992
SRM	5,424,154	6/13/1995	Borodovsky	430	5	12/10/1993
SRM	5,480,746	1/2/1996	Jinbo, et al.	430	5	5/16/1994
SRM	5,496,666	3/5/1996	Chu, et al.	430	5	10/27/1994
SRM	5,498,579	3/12/1996	Borodovsky, et al.	437	250	6/8/1994
SRM	5,503,951	4/2/1996	Flanders, et al.	430	5	4/17/1995
SRM	5,523,186	6/4/1996	Lin, et al.	430	5	12/16/1994
SRM	5,527,645	6/18/1996	Pati, et al.	430	5	11/17/1994
SRM	5,532,090	7/2/1996	Borodovsky	430	5	3/1/1995
SRM	5,537,648	7/16/1996	Liebmann, et al.	395	500	8/15/1994
SRM	5,538,815	7/23/1996	Oi, et al.	430	5	9/14/1993
SRM	5,539,568	7/23/1996	Lin, et al.	359	285	6/7/1995
SRM	5,565,286	10/15/1996	Lin	430	5	11/17/1994
SRM	5,573,890	11/12/1996	Spence	430	311	7/18/1994

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INFORMATION DISCLOSURE CITATION PTO-1449			Atty. Docket No. NMTI 1002-3 Applicant PIERRAT, Christophe Filing Date 8/17/2001		Serial No. 09/932,239 Group 1754 Not Yet Assigned	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SKM	5,595,843	1/21/1997	Dao	430	5	3/30/1995
SKM	5,620,816	4/15/1997	Dao	430	5	10/13/1995
SKM	5,635,316	6/3/1997	Dao	430	5	10/13/1995
SKM	5,636,131	6/3/1997	Liebmann, et al.	364	490	5/12/1995
SKM	5,702,848	12/30/1997	Spence	430	5	8/23/1996
SKM	5,725,969	3/10/1998	Lee	430	5	12/22/1995
SKM	5,761,075	6/2/1998	Oi, et al.	364	488	5/31/1996
SKM	5,766,804	6/16/1998	Spence	430	5	8/23/1996
SKM	5,766,806	6/16/1998	Spence	430	5	9/9/1996
SKM	5,807,649	9/15/1998	Liebmann, et al.	430	5	10/31/1996
SKM	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
SKM	5,858,580	1/12/1999	Wang, et al.	430	5	9/17/1997
SKM	5,885,734	3/23/1999	Pierrat, et al.	430	5	8/15/1996
SKM	5,923,566	6/13/1999	Galan, et al.	364	489	3/25/1997
SKM	5,994,002	11/30/1999	Matsuoka	430	5	9/4/1997
SKM	5,998,068	12/7/1999	Matsuoka	430	5	1/27/1998
SKM	6,004,702	12/21/1999	Lin	430	5	5/21/1998
SKM	6,010,807	1/4/2000	Lin	430	5	4/7/1998
SKM	6,057,063	5/2/2000	Liebmann, et al.	430	5	4/14/1997
SKM	6,066,180	5/23/2000	Kim, et al.	716	19	3/15/1999
SKM	6,077,630	6/20/2000	Pierrat	430	5	1/8/1998
SKM	6,083,275	7/4/2000	Heng, et al.	716	19	1/9/1998
SKM	6,228,539 B1	5/8/2001	Wang, et al.	430	5	1/12/1999

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U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SRM	6,251,549 B1	6/26/2001	Levenson	430	11	10/28/1999
SRM	6,258,493 B1	7/10/2001	Wang, et al.	430	5	7/17/2000

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SPM	2,650,962	5/16/1997	JP	—	—	<input type="checkbox"/>	<input type="checkbox"/>
SPM	EP 0 464 492 A1	1/8/1992	EP	—	—	<input type="checkbox"/>	<input type="checkbox"/>
SPM	EP 0 653 679 A2	5/17/1995	EP	—	—	<input type="checkbox"/>	<input type="checkbox"/>
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
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	Schmidt, R., et al., "Impact of Coma on CD Control for Multiphase PSM Designs", AMD, ASML (11 pages).		
	Erdmann, A., "Topography Effects and Wave Aberrations in Advanced PSM-Technology", Fraunhofer Institute of Integrated Circuits (11 pages).		
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	Lin, B.J., "The Relative Importance of the Building Blocks for 193nm Optical Lithography", Linnovation, Inc. (12 pages).		
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
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	Suzuki, A., et al., "Multilevel Imaging System Realizing k1= 3.1 Lithography", Canon Inc. (13 pages).		
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	Fritze, M., et al., "100-nm Node Lithography with KrF?", MIT Lincoln Lab, Numerical Technologies, Photronics, Arch Chemicals (14 pages).		
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		Applicant PIERRAT, Christophe	Group 1756 Not Yet Assigned
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